a second low concentration drain region of the second conductive type, provided in said first low concentration drain region, said second low concentration drain region being disposed close to an outer boundary of said first low concentration drain region and being higher in impurity concentration than at least an impurity concentration of the first low concentration drain region;

a high concentration source region of the second conductive type provided at another end of said gate electrode; and

a high concentration drain region of the second conductive type formed in said second low concentration drain region, said high concentration drain region being spaced away a predetermined distance from said gate electrode and being higher in impurity concentration than the second low concentration drain region.

2. (Amended) A semiconductor device according to Claim 1, wherein said first low concentration drain region and said second low concentration drain region are formed by utilizing two kinds of second conductive type impurities, and the two kinds of said second type conductive impurities have different diffusion coefficients.

3. (Amended) A semiconductor device according to Claim 1, wherein said first low concentration drain region and said second low concentration drain region are formed by using phosphorus ions and arsenic ions, respectively.--

Please add claims 8 to 14.

-- 8. (New) A semiconductor device according to Claim 1, wherein relatively, the first and second drain regions have low impurity concentrations and the third drain region has a high impurity concentration.

9. (New) A semiconductor device comprising:

a semiconductor substrate;

an gate oxide film provided on the semiconductor substrate;

a gate electrode disposed on the gate oxide film;

a first drain region provided at one end of said gate electrode in the semiconductor substrate;

a second drain region provided in said first drain region, an outer boundary of said second drain region being disposed close to an outer boundary of said first drain region;

a third drain region provided in said second drain region, said third drain region being spaced away a predetermined distance from said gate electrode and being spaced far apart from the outer boundary of the second drain region; and

a region of the second conductive type provided at another end of said gate electrode,

wherein the first, second, and third drain regions all having different impurity concentrations.

10. (New) A semiconductor device according to Claim 8, wherein the second drain region has a higher impurity concentration than the first drain region, and the third drain region has a higher impurity concentration than the second drain region.

11. (New) A semiconductor device according to Claim 8, wherein the first, second, and third drain regions and the source region are of a second conductivity type and the semiconductor substrate is of a first conductivity type.

12. (New) A semiconductor device according to Claim 8, wherein said first drain region and said second drain region are formed by utilizing two kinds of second conductive type impurities, and the two kinds of said second type conductive impurities have different diffusion coefficients.

13. (New) A semiconductor device according to Claim 8, wherein said first drain region and said second drain region are formed by using phosphorus ions and arsenic ions, respectively.

14. (New) A semiconductor device according to Claim 8, wherein the first, second and third drain regions form a triple well structure in the semiconductor substrate such that the third